SILICON MIRCROWAVE POWER TRANSISTOR

Part Number SD1546-1

SILICON MIRCROWAVE POWER TRANSISTOR

PRODUCT DATA SHEET

FEATURES:

MERICAN

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High Outpur Power 60 W @ 1.0 GHzHigh Gain Bandwidth Product $f_t = 6.0 \text{ GHz} @ \text{Ic} = 1.0\text{A}$ High Gain $G_{PE} = 7.5 \text{ dB} @ 1.0 \text{ GHz}$ High Reliability Gold Metallization Nitride Passivation Diffused Ballast Resistors Common Base Pin Configuration

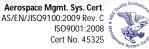
Absolute Maximum Ratings

SYMBOL	PARAMETERS	RATING	UNITS	
Vсво	Collector-Base Voltage	60	V	
Vceo	Collector-Emitter Voltage	30	V	
Vebo	Emitter-Base Voltage	3.0	V	
lc	Collector Current	6.0	А	
TJ	Junction Temperature	200	°C	
Тѕтс	Storage Temperature	-65 to 200	°C	
θıc	Thermal Resistance	9	°C /W	

PERFORMANCE DATA: Electrical Characteristics ($T_A = 25^{\circ}C$)

SYMBOL	PARAMETERS	CONDITIONS	UNIT	MIN.	TYP.	MAX.
P _{1dB}	Power output at 1 dB compression	f = 1.0 GHz	W		60	
η	Collector Efficiency	Class C	%		50	
hfe	Forward Current Transfer Ratio	Vсв = 28 V, Iс = 4.0 A		20	60	100
Ссв	Output Capacitance:	f = 1 MHz, I _E = 0	pF		60	
Р⊤	Total Power Dissipation	Vсв = 28V, Iс = 4.0 A	W		120	

Tel. 1-973-377-9566, Fax. 1-973-377-3078 133 Kings Road, Madison, New Jersey07940 United States of America © 2014 American Microsemiconductor, Inc. Specifications are subject to change without notice. Document Page 1 of 2 Revised 01/2014



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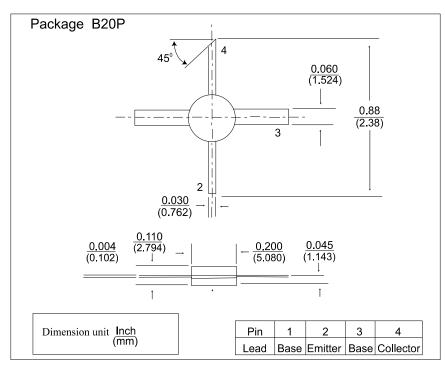
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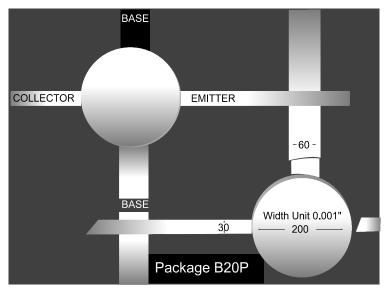
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SILICON MIRCROWAVE POWER TRANSISTOR

PACKAGE OUTLINE



MARKING / LEAD CONFIGURATION



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